Si Zener-diode Chip－TKAS06ZDN

1. Scope

- The specification applies to planar Zener diode.
- Extra lower leakage current
- Special thickness for special assembly process.

2. Structure

- Planar type Zener diode.
- Electrode P (anode)　　　：Aluminum. (Gold for option)
- Electrode N (cathode) side：Gold.

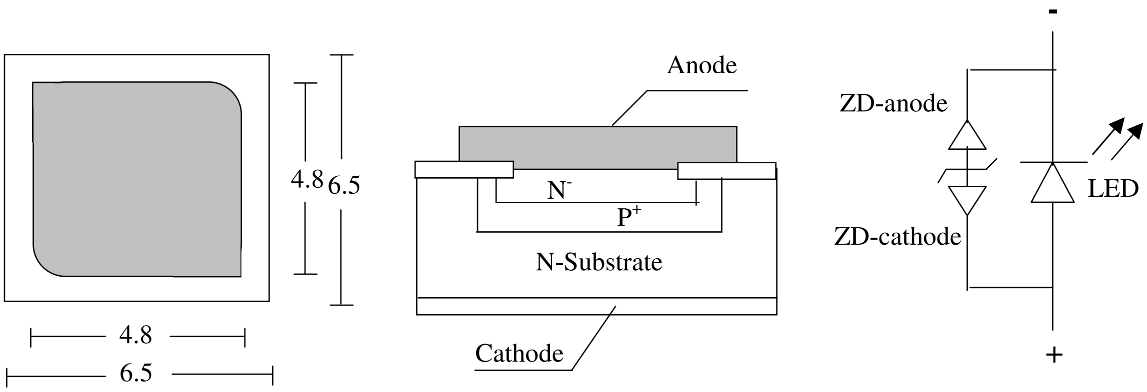
3. Size

- Chip size　　：6.5mil × 6.5mil ± 0.8mil (0.1651mm × 0.1651mm ± 0.020mm)
- Thickness　　：4.0mil /6.0± 0.6mil (0.110mm/0.150mm ± 0.015mm)
- Pad Size　　：4.8mil × 4.8mil ± 0.4mil (0.122mm × 0.122mm ± 0.010mm)
- Pattern drawing：per fig. 1

4. Electrical Characteristics

（Ta＝＋25 ℃）

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	Rank C: $I_F = 10mA$	5.5		7.8	V
Forward Leakage current	I_F	Rank C: $V_F = 5V$			500	nA
Reverse Voltage	Vz	Rank C: $I_R = 10mA$	5.5		7.8	V
Reverse Leakage current	I_R	Rank C: $V_R = 5V$			500	nA



Unit：mil

fig. 1　　　　2012.May